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(54) Title: DEPOSITION OF CARBON GAPFILL MATERIALS

200

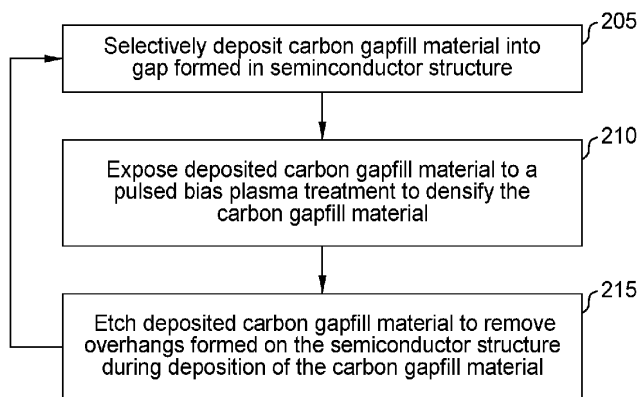


FIG. 2

(57) Abstract: The present disclosure provides methods and apparatus that facilitate the formation of high-quality carbon gapfill structures and that address the issues related to conventional carbon gapfill methods. In certain embodiments, the carbon gapfill methods and apparatus described herein include plasma enhanced CVD (PECVD) or flowable CVD (FCVD) processes to gapfill structures with high-quality, and stable carbon films.

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